

# NPN Epitaxial Silicon Transistor

## BC546 / BC547 / BC548 / BC549 / BC550

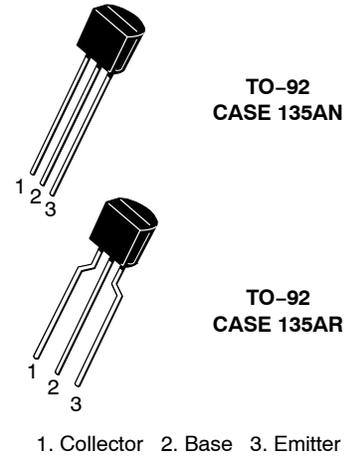
### Features

- Switching and Amplifier
- High-Voltage: BC546,  $V_{CEO} = 65\text{ V}$
- Low-Noise: BC549, BC550
- Complement to BC556, BC557, BC558, BC559, and BC560
- These are Pb-Free Devices

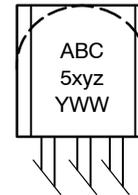
### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector-Base Voltage BC546 BC547 / BC550 BC548 / BC549	$V_{CBO}$	80 50 30	V
Collector-Emitter Voltage BC546 BC547 / BC550 BC548 / BC549	$V_{CEO}$	65 45 30	V
Emitter-Base Voltage BC546 / BC547 BC548 / BC549 / BC550	$V_{EBO}$	6 5	V
Collector Current (DC)	$I_C$	100	mA
Collector Power Dissipation	$P_C$	500	mW
Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-65 to +150	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



### MARKING DIAGRAM



BC5xyz = Device Code  
 x = 4 or 5  
 y = 6, 7, 8, 9 or 0  
 z = A, B, C  
 A = Assembly Location  
 Y = Year  
 WW = Work Week

### ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

## BC546 / BC547 / BC548 / BC549 / BC550

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 30\text{ V}, I_E = 0$			15	nA
$h_{FE}$	DC Current Gain	$V_{CE} = 5\text{ V}, I_C = 2\text{ mA}$	110		800	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$		90	250	mV
		$I_C = 100\text{ mA}, I_B = 5\text{ mA}$		250	600	
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$		700		mV
		$I_C = 100\text{ mA}, I_B = 5\text{ mA}$		900		
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 5\text{ V}, I_C = 2\text{ mA}$	580	660	700	mV
		$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$			720	
$f_T$	Current Gain Bandwidth Product	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}, f = 100\text{ MHz}$		300		MHz
$C_{ob}$	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		3.5	6.0	pF
$C_{ib}$	Input Capacitance	$V_{EB} = 0.5\text{ V}, I_C = 0, f = 1\text{ MHz}$		9		pF
NF	Noise Figure	BC546 / BC547 / BC548	$V_{CE} = 5\text{ V}, I_C = 200\text{ }\mu\text{A}, f = 1\text{ kHz}, R_G = 2\text{ k}\Omega$	2.0	10.0	dB
		BC549 / BC550		1.2	4.0	
		BC549	$V_{CE} = 5\text{ V}, I_C = 200\text{ }\mu\text{A}, R_G = 2\text{ k}\Omega, f = 30\text{ to }15000\text{ MHz}$	1.4	4.0	
		BC550		1.4	3.0	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### $h_{FE}$ CLASSIFICATION

Classification	A	B	C
$h_{FE}$	110 ~ 220	200 ~ 450	420 ~ 800

TYPICAL PERFORMANCE CHARACTERISTICS

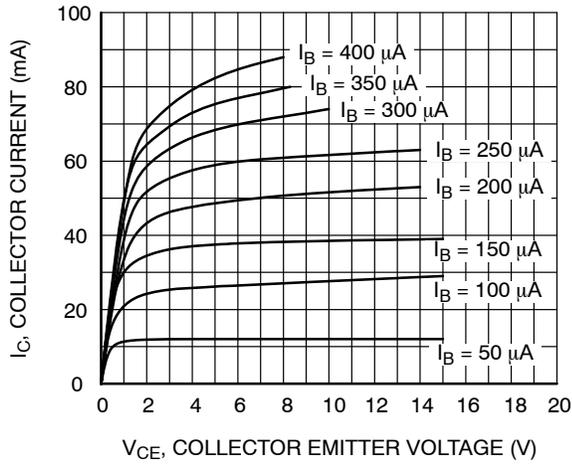


Figure 1. Static Characteristic

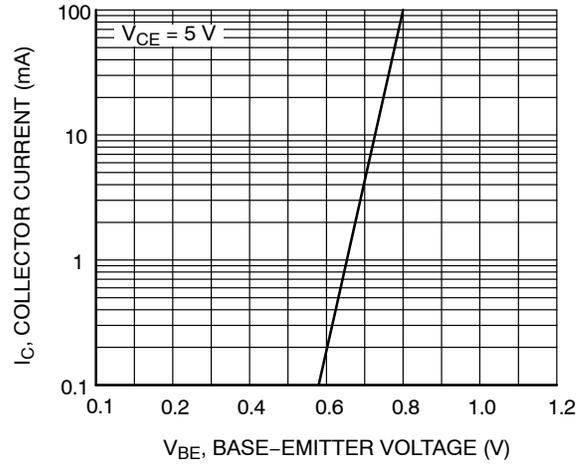


Figure 2. Transfer Characteristics

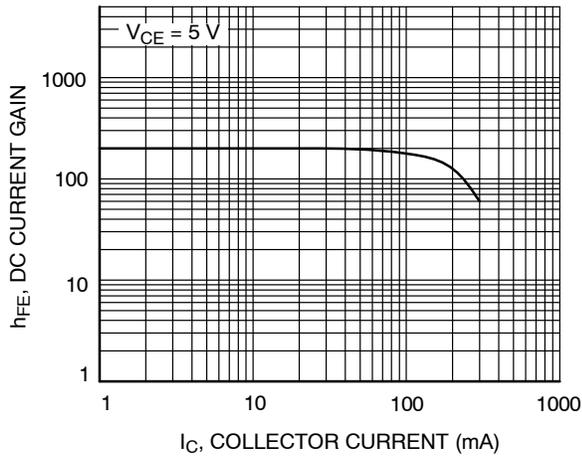


Figure 3. DC Current Gain

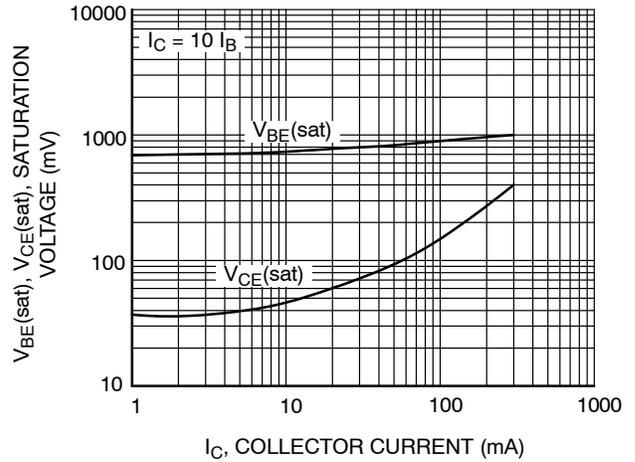


Figure 4. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

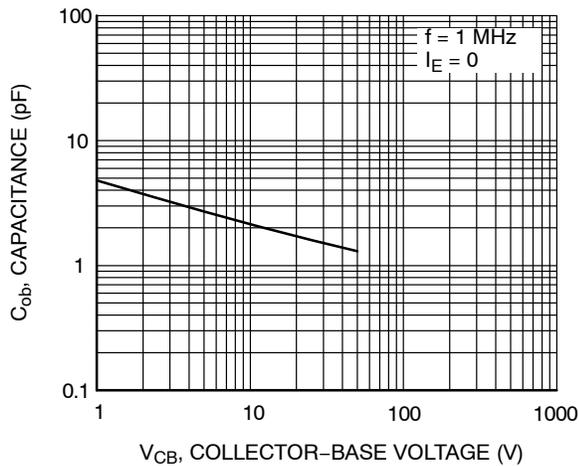


Figure 5. Output Capacitance

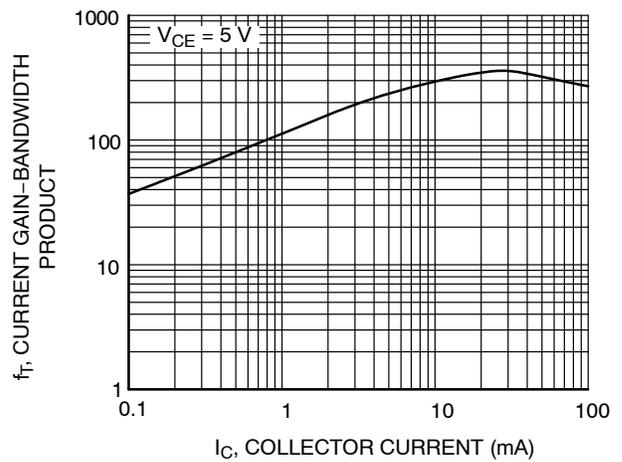
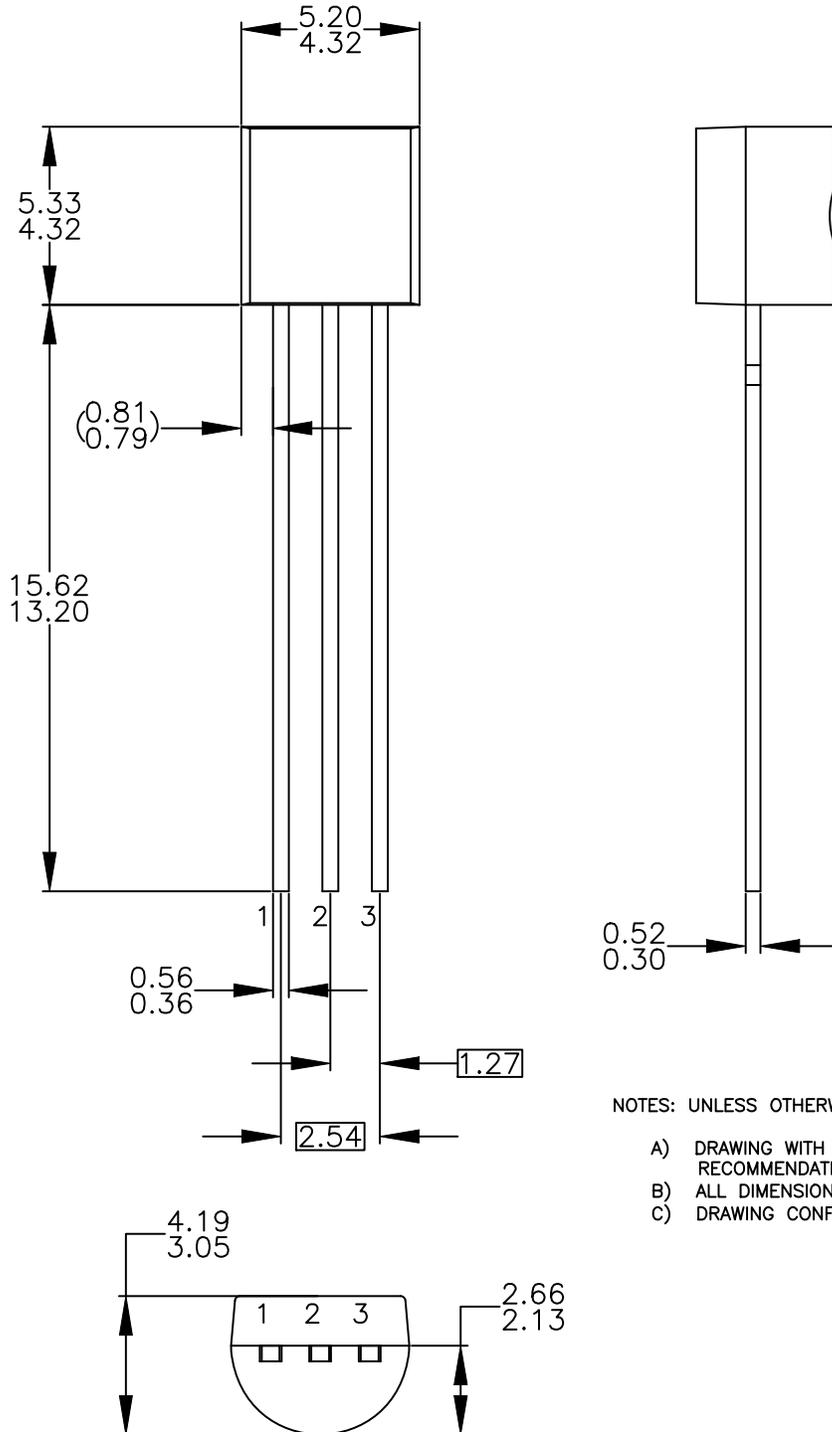


Figure 6. Current Gain Bandwidth Product

**MECHANICAL CASE OUTLINE**  
**PACKAGE DIMENSIONS**

TO-92 3 4.825x4.76  
CASE 135AN  
ISSUE O

DATE 31 JUL 2016



NOTES: UNLESS OTHERWISE SPECIFIED

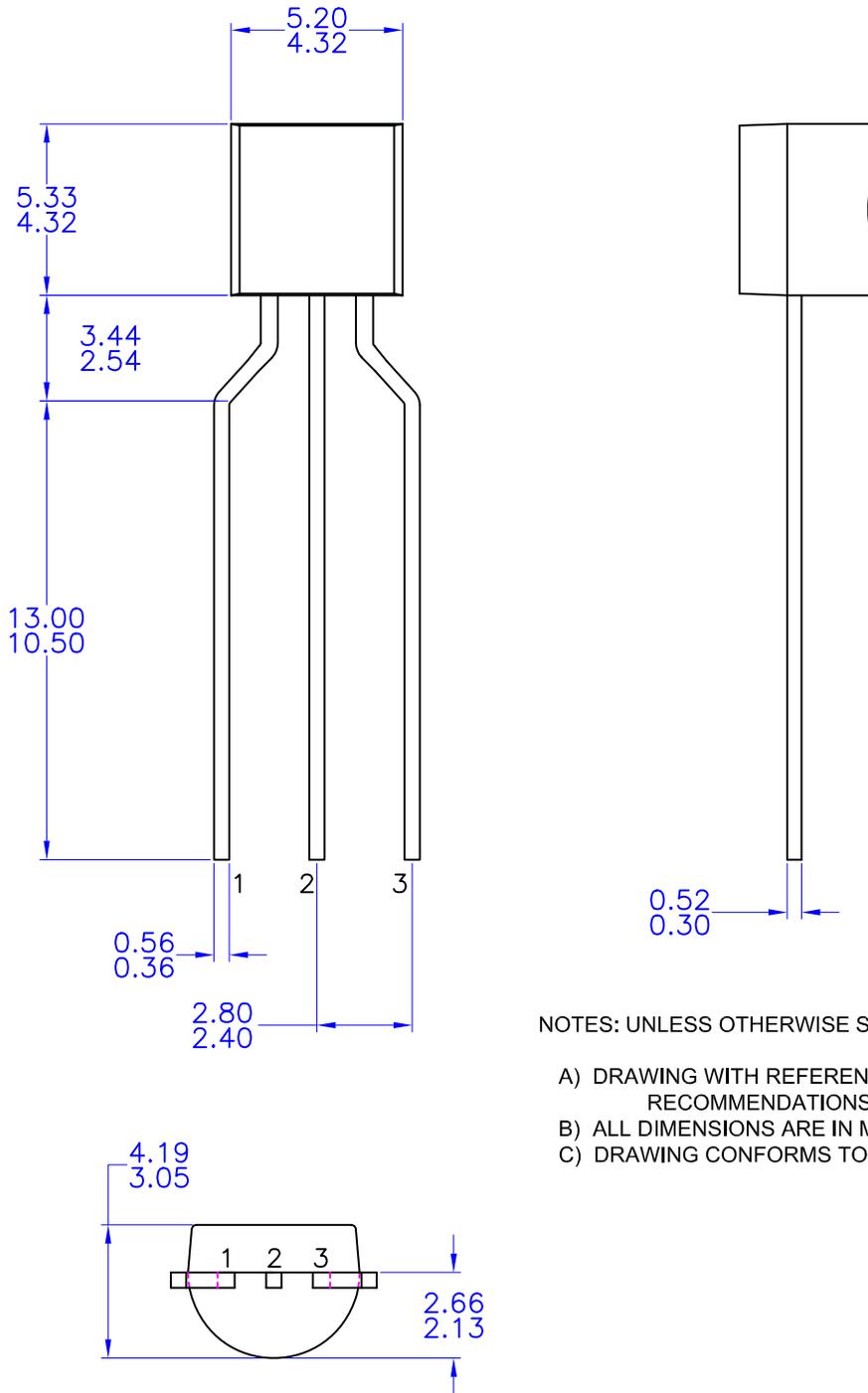
- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-2009.

<b>DOCUMENT NUMBER:</b>	<b>98AON13880G</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>TO-92 3 4.825X4.76</b>	<b>PAGE 1 OF 1</b>

ON Semiconductor and **ON** are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**TO-92 3 4.83x4.76 LEADFORMED**  
**CASE 135AR**  
**ISSUE O**

DATE 30 SEP 2016



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994

<b>DOCUMENT NUMBER:</b>	<b>98AON13879G</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>TO-92 3 4.83X4.76 LEADFORMED</b>	<b>PAGE 1 OF 1</b>

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.